Abstracts

100 W L-band GaAs power FP-HFET operated at 30 V

N. Sakura, K. Matsunaga, K. Ishikura, I. Takenaka, K. Asano, N. Iwata, M. Kanamori and M. Kuzuhara. "100 W L-band GaAs power FP-HFET operated at 30 V." 2000 MTT-S International Microwave Symposium Digest 00.3 (2000 Vol. III [MWSYM]): 1715-1718.

This paper reports an L-band power AlGaAs/GaAs heterostructure FET with a field-modulating plate (FP-HFET), which accomplished 100 W output power with a high power density of 1.16 W/mm at a drain bias voltage of 30 V. The developed FP-HFET is promising for achieving improved performance and reduced size of digital cellular base station systems.

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